What is claimed is:

1. A light-emitting apparatus having a light-emitting device comprising:

a first electrode;

a second electrode;

an electroluminescent film disposed between the first electrode and the second electrode;

a film containing fluoroplastics formed over the second electrode; and

an inorganic insulating film formed on the film containing fluoroplastics.

2. A light-emitting apparatus having a light-emitting device comprising:

a first electrode electrically connected to a TFT formed over a substrate via an insulating film;

a second electrode;

an electroluminescent film disposed between the first electrode and the second electrode;

a film containing fluoroplastics formed over the second electrode; and

an inorganic insulating film formed on the film containing fluoroplastics.

3. A light-emitting apparatus according to Claim 2,

wherein:

the insulating film comprises a first insulating film and a second insulating film formed on the first insulating film;

the first insulating film comprises a material selected from the group consisting of acrylic, polyamide, and polyimide; and

the second insulating film is a film containing fluoroplastics.

4. A light-emitting apparatus according to Claim 2, wherein the insulating film contains fluoroplastics.

5. A light-emitting apparatus according to Claim 1,

wherein the film containing fluoroplastics is one type of polymer selected from polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

6. A light-emitting apparatus according to Claim 3,

wherein:

the second insulating film is a mixed film comprising fluoroplastics and metallic oxides, and

a ratio of the metallic oxides in the mixed film monotonically increases from a portion of the mixed film distant from the first electrode to a portion of the mixed film close to the first electrode.

7. A fabrication method of a light-emitting apparatus having a light-emitting device including a first electrode, a second electrode, and an electroluminescent film disposed between the first electrode and the second electrode, comprising the steps of:

forming a film containing fluoroplastics over the second electrode by sputtering;

treating a surface of the film containing fluoroplastics with plasma; and

forming an inorganic insulating film on the film containing fluoroplastics.

8. A fabrication method of a light-emitting apparatus having a light-emitting device including a first electrode electrically connected to a TFT formed on a substrate via an insulating film, a second electrode, and an electroluminescent film disposed between the first electrode and the second electrode, comprising the steps of:

forming a film containing fluoroplastics over the second electrode by sputtering;

treating a surface of the film containing fluoroplastics with plasma; and

forming an inorganic insulating film on the film containing fluoroplastics.

9. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 8,

wherein:

the insulating film comprises a first insulating film and a second insulating film formed on the first insulating film;

the first insulating film comprises a material selected from the group consisting of acrylic, polyamide, and polyimide; and

the second insulating film is formed of a film containing fluoroplastics by sputtering on the first insulating film.

10. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 9,

wherein a surface of the second insulating film is processed in plasma employing Ar as process gas.

11. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 9 further comprising the steps of:

using sequentially a plurality of sputtering targets of metallic oxides, fluoroplastics, or mixture of metallic oxides and fluoroplastics; and

forming the second insulating film by high-frequency sputtering with applying from 0.15 to 6.2 W per square centimeter high frequency electric power;

wherein, ratios of metallic oxides in the second insulating film is increased with deposition time.

12. A light-emitting apparatus according to Claim 2,

wherein the film containing fluoroplastics is one type of polymer selected from polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

13. A light-emitting apparatus according to Claim 3,

wherein the film containing fluoroplastics is one type of polymer selected from polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

14. A light-emitting apparatus according to Claim 4,

wherein the film containing fluoroplastics is one type of polymer selected from

polytetrafluoroethylene, tetrafluoroethylene-hexafluoropropylene copolymer, polychlorotrifluoroethylene, tetrafluoroethylene-ethylene copolymer, polyvinyl fluoride, and polyvinylidene fluoride.

15. A light-emitting apparatus according to Claim 4,

wherein:

the insulating film is a mixed film comprising fluoroplastics and metallic oxides, and

a ratio of the metallic oxides in the mixed film monotonically increases from a portion of the mixed film distant from the first electrode to a portion of the mixed film close to the first electrode.

16. A fabrication method of a light-emitting apparatus having a light-emitting device according to Claim 10 further comprising the steps of:

using sequentially a plurality of sputtering targets of metallic oxides, fluoroplastics, or mixture of metallic oxides and fluoroplastics; and

forming the second insulating film by high-frequency sputtering with applying from 0.15 to 6.2 W per square centimeter high frequency electric power;

wherein, ratios of metallic oxides in the second insulating film is increased with deposition time.